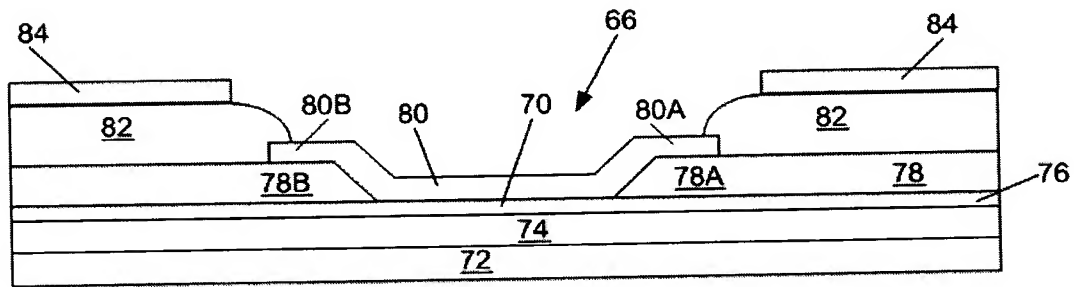
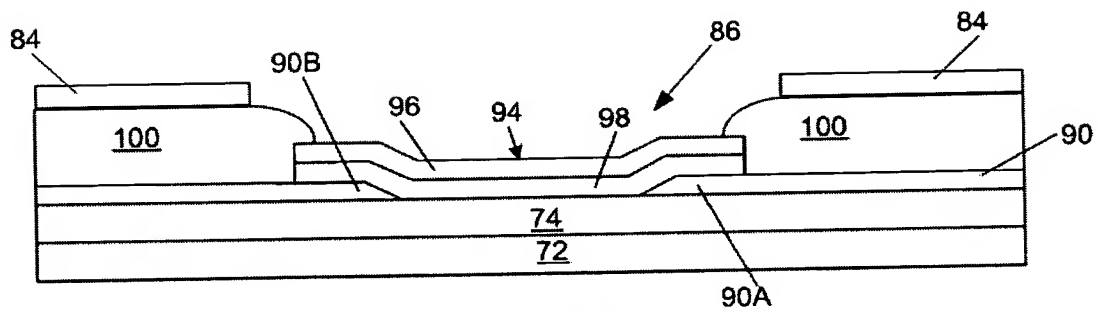


**Fig. 1**

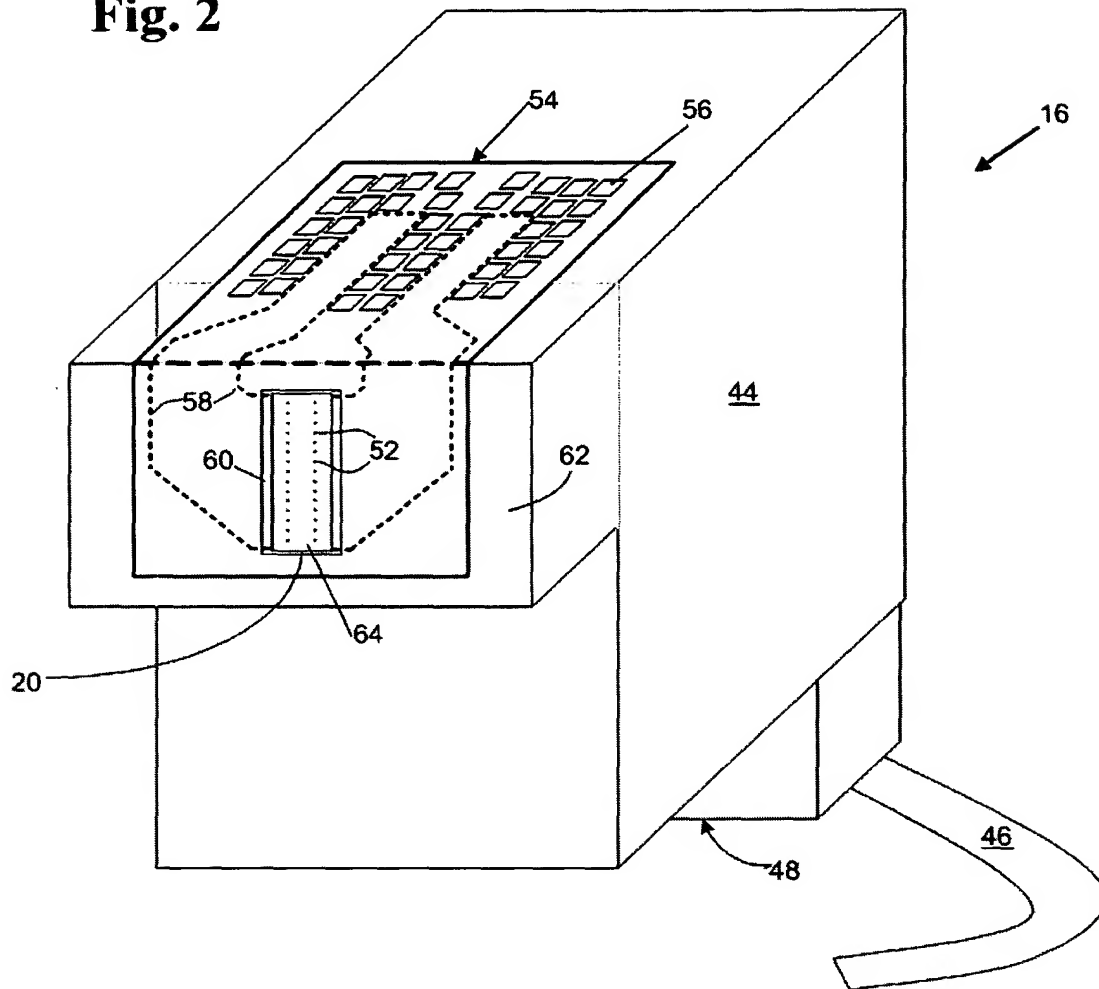


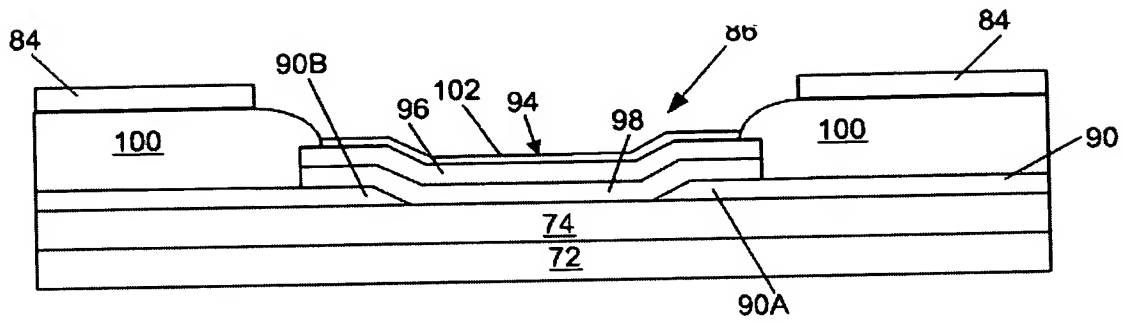
**Fig. 3**



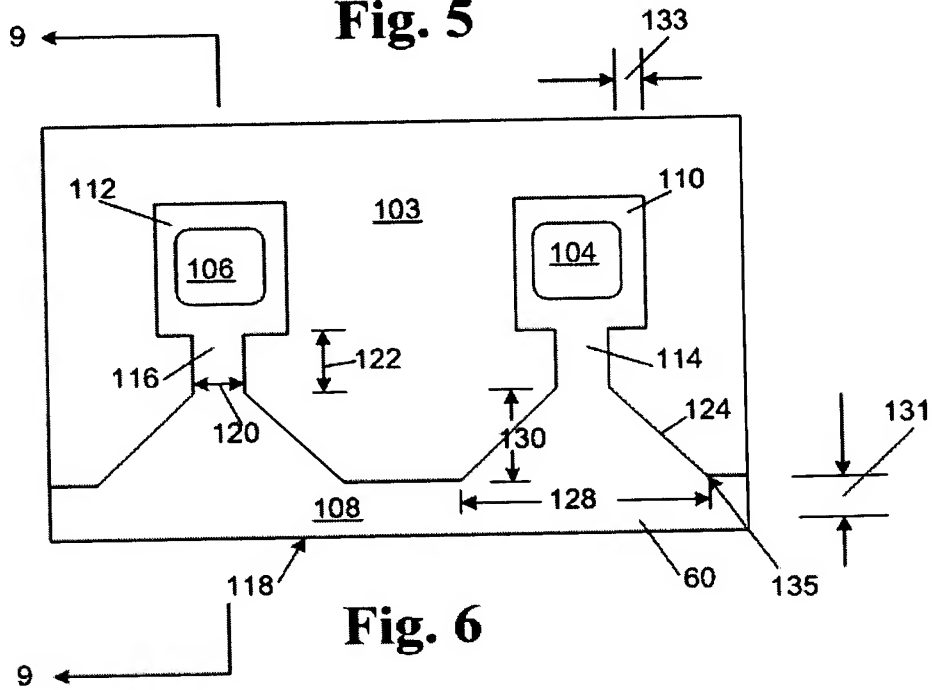
**Fig. 4**

**Fig. 2**

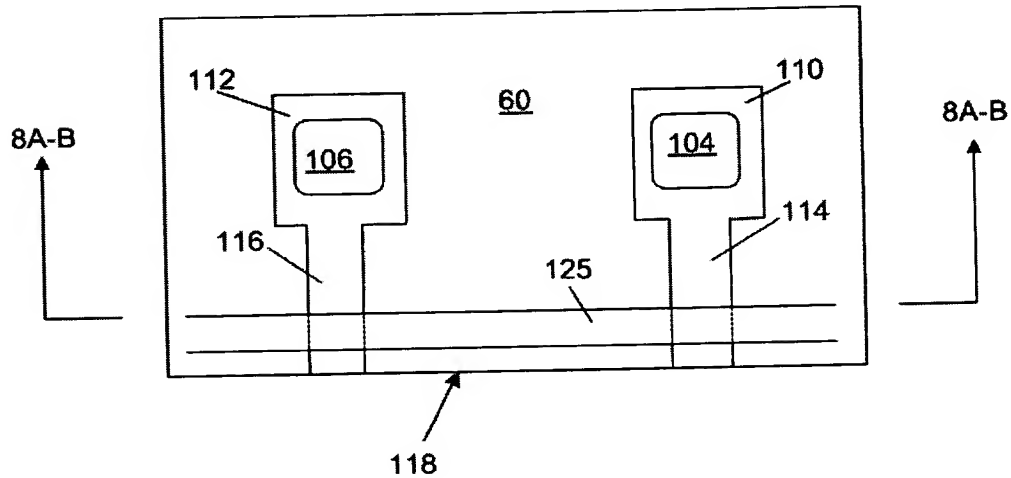




**Fig. 5**



**Fig. 6**



**Fig. 7**

FIG. 1 is a cross-sectional view of a semiconductor device. The device includes a substrate 60 with a top surface 121. Two rectangular regions 110 and 112 are defined by dashed lines. Within these regions are structures 114 and 116, respectively. Below these structures are layers 119 and 117. A vertical dimension line on the right indicates a thickness of 123.

**Fig. 9**

This diagram shows a cross-section of a device with a central channel 104. Above the channel are two large rectangular blocks, 132 on the left and 103 on the right, separated by a gap 110. The top surface of the entire structure is labeled 64. Below the channel 104 is a thin layer 84. The bottom-most layer is indicated by dimension 60. Various dimensions are provided: 266 for the total height, 134 for the width of the gap 110, 270 for the angle of the sloped side of block 132, 52 for the width of the top edge of block 132, 132 for the width of block 132, and 136 for the width of the central channel 104.

**Fig. 9**

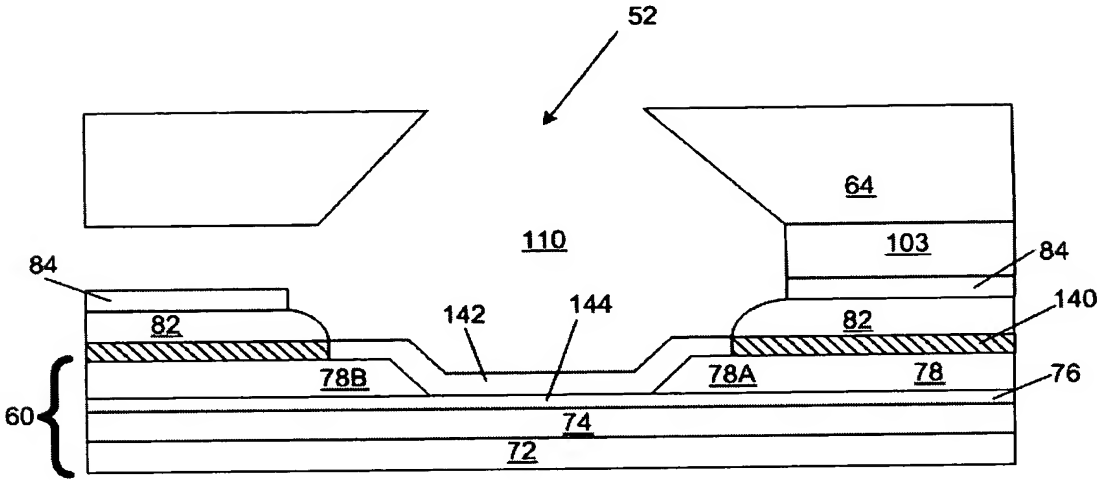


Fig. 10

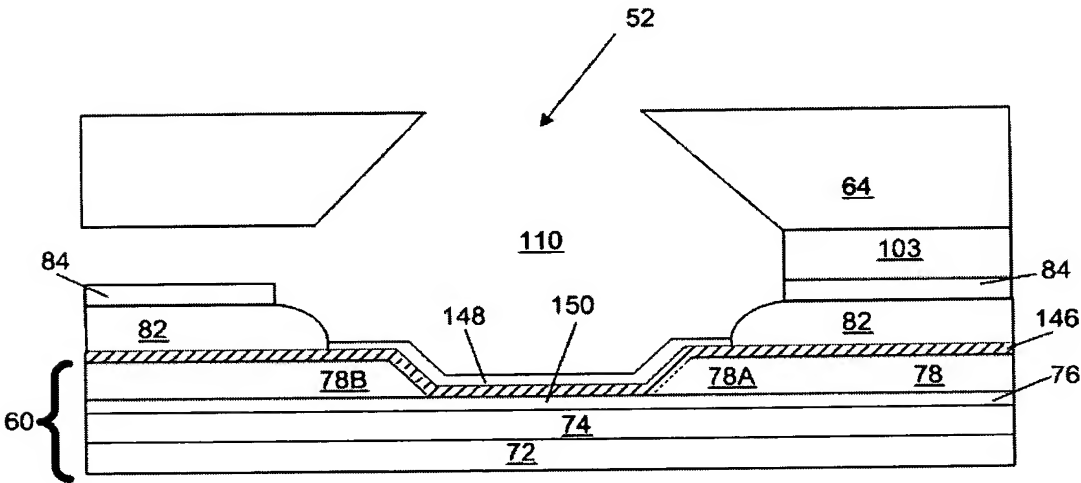
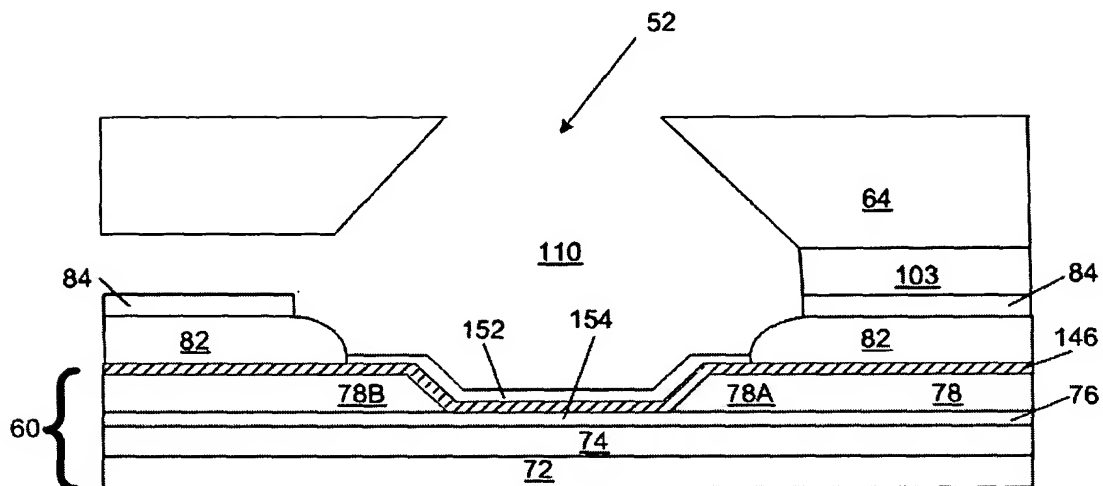
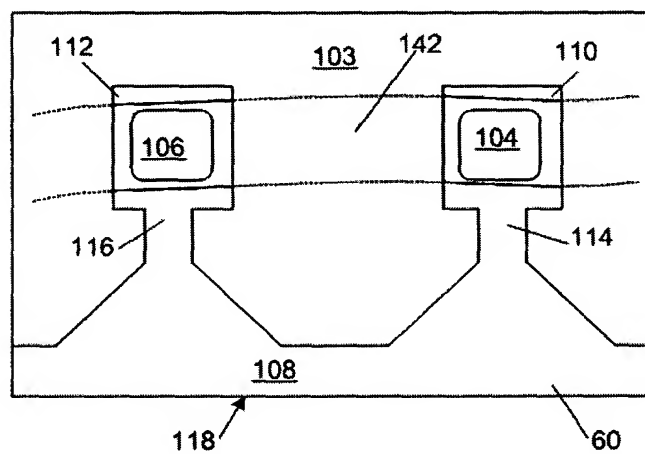


Fig. 11



**Fig. 12**



**Fig. 13**

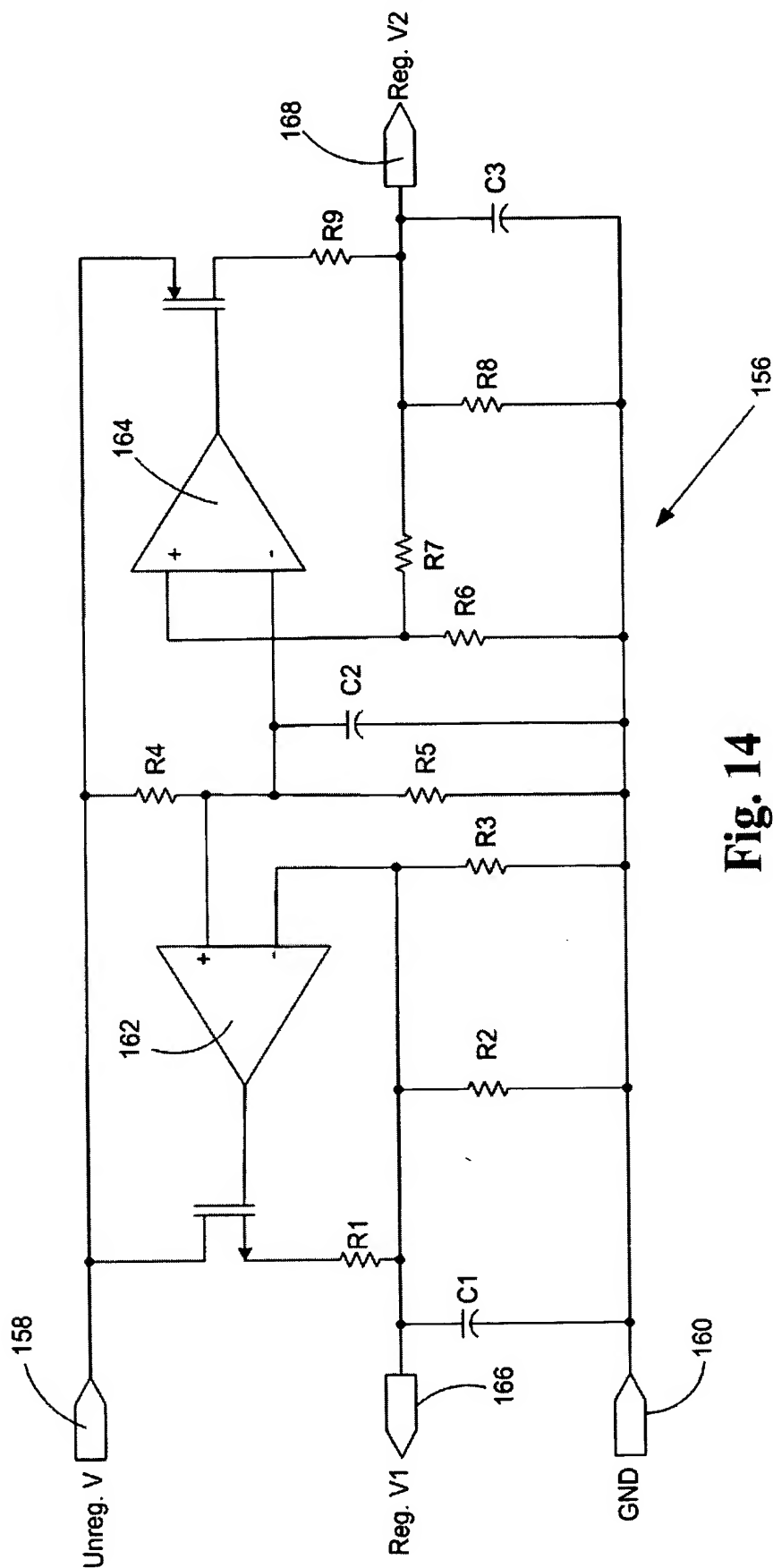
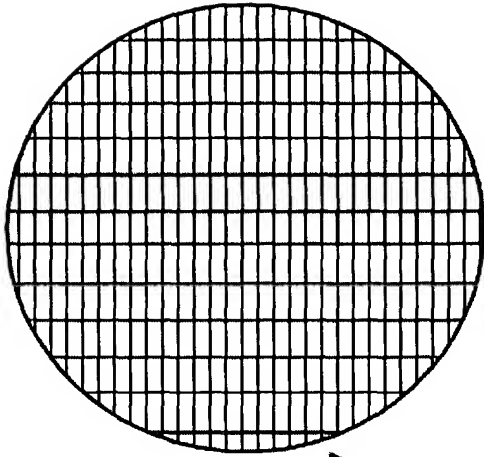
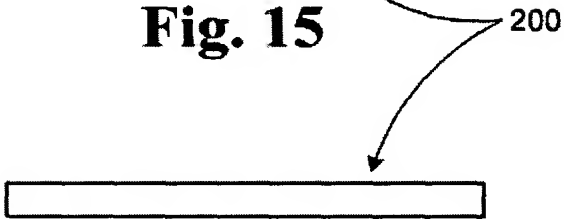


Fig. 14



**Fig. 15**



**Fig. 16**



**Fig. 18**